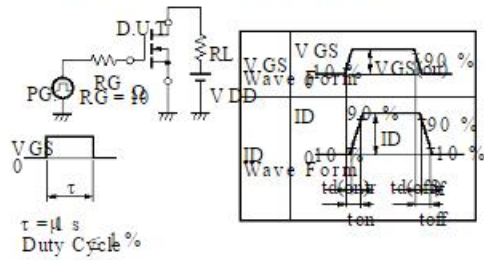


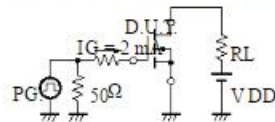
ELECTRICAL CHARACTERISTICS (TA = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN	TYPE	MAX	UNIT
Drain to Source On-state Resistance	$R_{DS(on)}$	$V_{GS} = 4.0\text{ V}, I_D = 3.5\text{ A}$		19	27	$m\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 3.5\text{ A}$		25	40	$m\Omega$
Gate to Source Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	0.5	0.9	1.5	V
Forward Transfer Admittance	y_{fs}	$V_{DS} = 10\text{ V}, I_D = 3.5\text{ A}$	6.0	13		S
Drain Leakage Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			10	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = +12\text{ V}, V_{DS} = 0\text{ V}$			+10	μA
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}$		1040		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$		340		pF
Reverse Transfer Capacitance	C_{rss}	$f = 1\text{ MHz}$		150		pF
Turn-on Delay Time	$t_{d(on)}$	$I_D = 3.5\text{ A}$		25		ns
Rise Time	t_r	$V_{GS(on)} = 4.0\text{ V}$		120		ns
Turn-off Delay Time	$t_{d(off)}$	$V_{DD} = 15\text{ V}$		73		ns
Fall Time	t_f	$R_G = \infty$		77		ns
Total Gate Charge	Q_G	$I_D = 7.0\text{ A}$		13.7		nC
Gate to Source Charge	Q_{GS}	$V_{DD} = 24\text{ V}$		1.8		nC
Gate to Drain Charge	Q_{GD}	$V_{GS} = 4.0\text{ V}$		5.8		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 7.0\text{ A}, V_{GS} = 0\text{ V}$		0.77		V
Reverse Recovery Time	t_{rr}	$I_F = 7.0\text{ A}, V_{GS} = 0\text{ V}$		31		ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100\text{ A}/\mu\text{s}$		58		nC

TEST CIRCUIT 1 SWITCHING TIME



TEST CIRCUIT 2 GATE CHARGE



TYPICAL CHARACTERISTICS (TA = 25 °C)

